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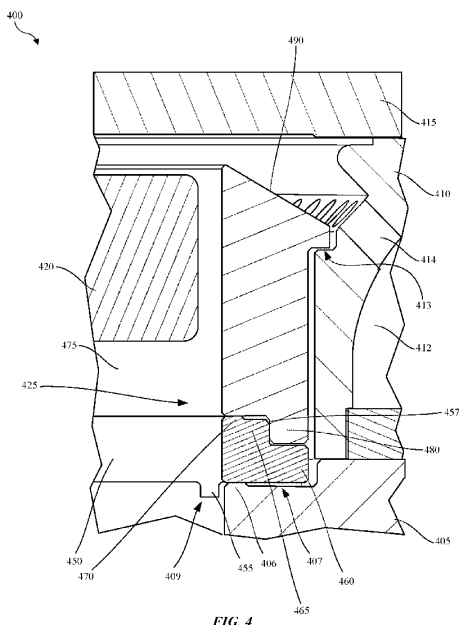
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(54) Title: TWO-PIECE RF SHIELD DESIGN



(57) Abstract: Exemplary semiconductor processing chambers may include a chamber body. The chambers may include a substrate support assembly disposed within the chamber body. The chambers may include a substrate support assembly having a support plate seated atop a support stem. The chambers may include a radio frequency (RF) shield seated atop the chamber body and extending about a peripheral edge of the support plate. The RF shield may include a lower annular member. The RF shield may include an upper annular member seated atop the lower annular member. The upper annular member may define a lip that protrudes radially outward from an outer surface of the upper annular member. Each of the lower annular member and the upper annular member may include a dielectric material.

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